

Jamal Bougdira

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7153009/publications.pdf>

Version: 2024-02-01

50
papers

984
citations

394421

19
h-index

477307

29
g-index

50
all docs

50
docs citations

50
times ranked

1075
citing authors

#	ARTICLE	IF	CITATIONS
1	Morphological and optoelectrical study of ZnO:In/p-Si heterojunction prepared by ultrasonic spray pyrolysis. <i>Thin Solid Films</i> , 2017, 628, 36-42.	1.8	13
2	Silicon Carbon Nitride Thin Films Deposited by Pulsed Microwave Plasma Assisted Chemical Vapour Deposition. <i>Journal of Applied Sciences</i> , 2017, 17, 306-314.	0.3	0
3	Sulfide precursor concentration and lead source effect on PbS thin films properties. <i>Journal of Alloys and Compounds</i> , 2016, 666, 327-333.	5.5	29
4	Properties of (NiO) ₁ -(ZnO) thin films deposited by spray pyrolysis. <i>Thin Solid Films</i> , 2016, 605, 116-120.	1.8	9
5	Formation mechanism of graphite hexagonal pyramids by argon plasma etching of graphite substrates. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 495304.	2.8	10
6	Dynamics of dust particles in a collisional radio-frequency plasma sheath. <i>Physica Scripta</i> , 2014, T161, 014052.	2.5	3
7	Microwave Plasma Process for SiCN:H Thin Films Synthesis with Composition Varying from SiC:H to SiN:H in H ₂ /N ₂ /Ar/Hexamethyldisilazane Gas Mixture. <i>Plasma Processes and Polymers</i> , 2014, 11, 551-558.	3.0	13
8	Plasma synthesis of hexagonal-pyramidal graphite hillocks. <i>Carbon</i> , 2014, 76, 330-340.	10.3	13
9	Deposition of tin(II) sulfide thin films by ultrasonic spray pyrolysis: Evidence of sulfur exo-diffusion. <i>Materials Science in Semiconductor Processing</i> , 2014, 17, 38-42.	4.0	35
10	Characterization of energetic and thermalized sputtered atoms in pulsed plasma using time-resolved tunable diode-laser induced fluorescence. <i>Applied Physics Letters</i> , 2014, 105, 181120.	3.3	15
11	Chemical bath composition effect on the properties of electrodeposited CuInSe ₂ thin films. <i>Journal of Alloys and Compounds</i> , 2014, 587, 303-307.	5.5	9
12	Influence of Sn content on properties of ZnO:SnO ₂ thin films deposited by ultrasonic spray pyrolysis. <i>Materials Science in Semiconductor Processing</i> , 2013, 16, 2021-2027.	4.0	36
13	Retrieving particle size and density from extinction measurement in dusty plasma, Monte Carlo inversion and Ray-tracing comparison. <i>Journal of Quantitative Spectroscopy and Radiative Transfer</i> , 2013, 128, 18-26.	2.3	19
14	Agglomeration processes sustained by dust density waves in Ar/C ₂ H ₂ plasma: From C ₂ H ₂ injection to the formation of an organized structure. <i>Physics of Plasmas</i> , 2013, 20, 033703.	1.9	3
15	Microstructure and opto-electrical properties of SnO ₂ :In ₂ O ₃ alloys thin films prepared by ultrasonic spray. <i>International Journal of Nanoparticles</i> , 2013, 6, 252.	0.3	0
16	Cluster Agglomeration Induced by Dust-Density Waves in Complex Plasmas. <i>Physical Review Letters</i> , 2012, 109, 245002.	7.8	21
17	Cu ₂ ZnSnS ₄ thin films deposition by ultrasonic spray pyrolysis. <i>Journal of Alloys and Compounds</i> , 2012, 542, 22-27.	5.5	99
18	Wide variations of SiC _x N _y :H thin films optical constants deposited by H ₂ /N ₂ /Ar/hexamethyldisilazane microwave plasma. <i>Surface and Coatings Technology</i> , 2012, 208, 46-50.	4.8	23

#	ARTICLE	IF	CITATIONS
19	Structural and optical properties of a-SiCN thin film synthesised in a microwave plasma at constant temperature and different flow of CH ₄ added to HMDSN/N ₂ /Ar mixture. Surface and Coatings Technology, 2011, 205, S214-S217.	4.8	22
20	Characterization of a neutral atomic hydrogen source developed in the perspective of carbon materials etching study. Surface and Coatings Technology, 2011, 205, S384-S387.	4.8	3
21	The influence of CH ₄ addition on composition, structure and optical characteristics of SiCN thin films deposited in a CH ₄ /N ₂ /Ar/hexamethyldisilazane microwave plasma. Thin Solid Films, 2011, 520, 245-250.	1.8	35
22	Photoluminescence, FTIR and X-ray diffraction studies on undoped and Al-doped ZnO thin films grown on polycrystalline α -alumina substrates by ultrasonic spray pyrolysis. Journal of Luminescence, 2010, 130, 2113-2117.	3.1	94
23	Electrical resistivity and photoluminescence of zinc oxide films prepared by ultrasonic spray pyrolysis. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 106-115.	1.8	45
24	Characterization of a N ₂ /CH ₄ Microwave Plasma With a Solid Additive Si Source Used for SiCN Deposition. Plasma Processes and Polymers, 2009, 6, S576.	3.0	10
25	Controlled Nanostructuration of Catalyst Particles for Carbon Nanotubes Growth. Journal of Physical Chemistry C, 2009, 113, 8718-8723.	3.1	10
26	Transparent and conducting ZnO films grown by spray pyrolysis. Semiconductor Science and Technology, 2009, 24, 035006.	2.0	26
27	Surface roughness of AlN films deposited on negatively biased silicon and diamond substrates. Diamond and Related Materials, 2009, 18, 1393-1400.	3.9	10
28	Role of silicon on the growth mechanisms of CN _x and SiCN thin films by N ₂ /CH ₄ microwave plasma assisted chemical vapour deposition. Surface and Coatings Technology, 2008, 203, 277-283.	4.8	11
29	Experimental and theoretical investigations of absorbance spectra for edge-plasma monitoring in fusion reactors. Journal of Quantitative Spectroscopy and Radiative Transfer, 2008, 109, 1549-1562.	2.3	10
30	Synthesis of carbon coated β -SiC nanofibers by microwave plasma assisted chemical vapour deposition in CH ₄ /H ₂ gas mixture. Diamond and Related Materials, 2008, 17, 1660-1665.	3.9	5
31	Transmission electron microscopy study of carbon nanostructures grown by MPACVD in CH ₄ /CO ₂ gas mixture. Diamond and Related Materials, 2007, 16, 1244-1249.	3.9	3
32	Preliminary Synthesis of Carbon Nitride Thin Films by N ₂ /CH ₄ Microwave Plasma Assisted Chemical Vapour Deposition: Characterisation of the Discharge and the Obtained Films. Plasma Processes and Polymers, 2007, 4, S210-S214.	3.0	7
33	Growth and characterisation of carbon nanostructures obtained by MPACVD system using CH ₄ /CO ₂ gas mixture. Diamond and Related Materials, 2006, 15, 1041-1046.	3.9	34
34	Influence of gas temperature on the loss mechanisms of H-atoms in a pulsed microwave discharge identified by time-resolved LIF measurements. Plasma Sources Science and Technology, 2006, 15, 526-532.	3.1	12
35	Correlation between the characteristics of a pulsed microwave plasma used for diamond growth and the properties of the produced films. Surface and Coatings Technology, 2005, 200, 1110-1116.	4.8	8
36	Characterization of ZnO/diamond SAW devices elaborated on the smooth nucleation side of MPACVD diamond. Physica Status Solidi A, 2005, 202, 2217-2223.	1.7	4

#	ARTICLE	IF	CITATIONS
37	Experimental study of a pulsed microwave plasma assisted chemical vapour deposition of carbon nanotubes. <i>Physica Status Solidi A</i> , 2005, 202, 2079-2084.	1.7	4
38	Freestanding CVD diamond elaborated by pulsed-microwave-plasma for ZnO/diamond SAW devices. <i>Diamond and Related Materials</i> , 2004, 13, 581-584.	3.9	56
39	Time-resolved plasma diagnostics for a better understanding of the improvement of pulsed MWPCVD of diamond. <i>Journal Physics D: Applied Physics</i> , 2001, 34, 896-904.	2.8	22
40	Influence of nitrogen incorporation on the electrical properties of MPCVD diamond films growth in CH ₄ -CO ₂ -N ₂ and CH ₄ -H ₂ -N ₂ gas mixtures. <i>Thin Solid Films</i> , 2000, 374, 27-33.	1.8	7
41	Optical emission diagnostics of permanent and pulsed microwave discharges in H ₂ -CH ₄ -N ₂ for diamond deposition. <i>Surface and Coatings Technology</i> , 1999, 116-119, 1233-1237.	4.8	10
42	Combined effect of nitrogen and pulsed microwave plasma on diamond growth using CH ₄ -CO ₂ gas mixture. <i>Thin Solid Films</i> , 1998, 325, 7-13.	1.8	11
43	Mechanisms of diamond films deposition from MPACVD in methane-hydrogen and nitrogen mixtures. <i>Surface and Coatings Technology</i> , 1998, 98, 1013-1019.	4.8	15
44	Influence of mechanical and chemical silicon surface preparation on diamond nucleation and growth in CH ₄ /H ₂ system discharge. <i>Surface and Coatings Technology</i> , 1998, 106, 53-59.	4.8	10
45	Combined effect of nitrogen and pulsed microwave plasma on diamond growth. <i>Diamond and Related Materials</i> , 1997, 6, 505-510.	3.9	23
46	Effect of nitrogen concentration on plasma reactivity and diamond growth in a H ₂ -CH ₄ -N ₂ microwave discharge. <i>Diamond and Related Materials</i> , 1997, 6, 107-119.	3.9	39
47	Spectroscopic investigation of a temporal post-discharge plasma for iron nitriding. <i>Plasma Sources Science and Technology</i> , 1992, 1, 117-121.	3.1	16
48	Effects of hydrogen on iron nitriding in a pulsed plasma. <i>Journal Physics D: Applied Physics</i> , 1991, 24, 1076-1080.	2.8	34
49	Low frequency d.c. pulsed plasma for iron nitriding. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 1991, 139, 15-19.	5.6	28
50	Material effects of titanium and titanium alloys on hollow cathode discharge characteristics. <i>Journal Physics D: Applied Physics</i> , 1991, 24, 672-676.	2.8	10